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supplying a reaction gas into said chamber under a reduced pressure;

C1 applying a first high-frequency power to said second electrode disposed below a central portion of said substrate and applying a second high-frequency power to said third electrode disposed below corner portions of said substrate to supply an AC electric field between said first electrode and said second and third electrodes;

generating plasma between said first electrode and said second and third electrodes; and

etching a material film on said substrate disposed on said second and third electrodes,

wherein said second electrode is flush with said third electrode.

C2 18. (Amended) An etching method using a dry etching apparatus, the method comprising the steps of:

disposing a substrate on a plurality of electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to an electrode disposed below a central portion of said substrate and applying

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a second high-frequency power to electrodes disposed below corner portions of said substrate;

generating plasma with a magnetic field or an electric field; and

etching a material film on said substrate disposed on said plurality of electrodes,

wherein said plurality of electrodes are flush with each other.

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20. (Amended) A method of forming a wiring, the method comprising the steps of:

forming a conductive film on a substrate;

selectively forming a mask on said conductive film;

disposing said substrate on at least first and second electrodes provided in a chamber provided with a third electrode opposed to said first and second electrodes;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to said first electrode disposed below a central portion of said substrate and applying a second high-frequency power to said second electrode disposed below corner portions of said substrate to apply an AC

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electric field between said third electrode and said first and second electrodes;

generating plasma between said third electrode and said first and second electrodes; and

selectively etching said conductive film on said substrate, wherein said first electrode is flush with said second electrode.

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22. (Amended) An etching method using a dry etching apparatus,

providing at least first, second and third electrodes being independent from each other, said first electrode being opposed to said second and third electrodes, and at least first, second, third high-power sources independently connected to each of said first, second and third electrodes, respectively, the method comprising the steps of:

disposing a substrate on said second and third electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

generating plasma between said first electrode and said second and third electrodes; and

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etching a material film on said substrate disposed on said second and third electrodes,

wherein said second and third electrodes are disposed so that an electric power applied to an entire surface of said substrate becomes uniform,

wherein said second electrode is flush with said third electrode.

24. (Amended) A method of manufacturing a semiconductor device using a dry etching apparatus,

providing at least first, second and third electrodes being independent from each other, said first electrode being opposed to said second and third electrodes,

forming a material film on a substrate;

selectively forming a mask on said material film;

disposing said substrate on said second and third electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to said second electrode disposed below a central portion of said substrate and applying a second high-frequency power to said third electrode disposed below corner portions of said substrate;

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generating plasma between said first electrode and said second and third electrodes; and

etching a material film on said substrate disposed on said second and third electrodes,

wherein said second electrode is flush with said third electrode.

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26. (Amended) An etching method comprising:

providing at least first and second electrodes and at least first and second high-power sources independently connected to each of said first and second electrodes;

disposing a substrate on said first and second electrodes provided in a chamber;

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supplying a reaction gas into said chamber under a reduced pressure;

generating plasma; and

etching a material film on said substrate disposed on said first and second electrodes,

wherein said first and second electrodes are disposed so that an electric power applied to an entire surface of said substrate becomes uniform,

wherein said first electrode is flush with said second electrode.

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27. (Amended) A method of manufacturing a semiconductor device comprising:

providing at least first and second electrodes,

forming a material film on a substrate;

selectively forming a mask on said material film;

disposing said substrate on said first and second electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to said first electrode disposed below a central portion of said substrate and applying a second high-frequency power to said third electrode disposed below corner portions of said substrate;

generating plasma; and

etching a material film on said substrate disposed on said first and second electrodes

wherein said first electrode is flush with said second electrode.

Please add the following new claim:

29. (New) An etching method comprising:

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(Fig. 1c, 3B)
(P. 11, line 7-9)

providing at least first, second, third, fourth and fifth electrodes and at least first, second, third, fourth and fifth high-power sources independently connected to each of said first, second, third, fourth and fifth electrodes;

disposing a substrate on said first, second, third, fourth and fifth electrodes provided in a chamber, wherein said first electrode is located below a central portion of said substrate and second, third, fourth and fifth electrodes are located below corner portions of said substrate;

supplying a reaction gas into said chamber under a reduced pressure;

generating plasma; and

etching a material film on said substrate,

wherein said first, second, third, fourth and fifth electrodes are disposed so that an electric power applied to an entire surface of said substrate becomes uniform, and

wherein said first, second, third, fourth and fifth electrodes are flush with each other.